

9/132,157

Abstract of the Disclosure

5 A PMOS transistor is formed in a CMOS integrated circuit, having a $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterojunction between the channel region and the substrate. The method is applicable to large volume CMOS IC fabrication. Germanium is implanted into a silicon substrate, through a gate oxide layer. The substrate is then annealed in a low temperature furnace, to form $\text{Si}_{1-x}\text{Ge}_x$ in the channel region.

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